In the Specification

Please replace the paragraph beginning at page 14, line 16 with the following replacement paragraph:

Figure 6 illustrates one embodiment of a magnetic memory device 600, e.g., magnetic random access memory (MRAM). Memory elements of MRAM have at least two magnetically stable states that can be written to and read from electronically. A memory device 600, such as MRAM, may be implemented as a solid-state non-volatile magnetic storage device in which each bit of data is stored in a magnetoresistive element 610, such as a magnetic tunnel transistor incorporating a magnetic tunnel junction. Magnetic tunnel transistors are described in commonly owned U.S. Patent Application Number 10/428,474, ~~identified by Docket Number HSJ920030006US1/00507.0500-US-01, and~~ filed on May 2, 2003, which is incorporated herein by reference in its entirety.

Please replace the paragraph beginning at page 21, line 19 with the following replacement paragraph.

A barrier layer 914 may be formed adjacent to the first magnetic layer 919. The barrier layer 915 may be comprised, for example, of AlOx having a thickness in a range of about 3 to about 6 Å [[Å]]. A second magnetic layer 912 may be formed adjacent to the barrier layer 914. The second magnetic layer formed of a ferromagnetic material, such as CoFe, or NiFe. The second magnetic layer may be a layered structure, as illustrated in Figures 9A and 9B, of ferromagnetic materials. A cap layer 910 may be formed adjacent the second magnetic layer 912.